



### Features

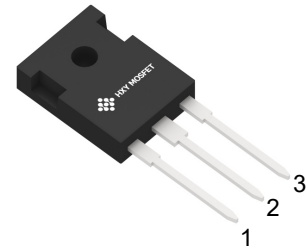
- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)
- Halogen free, RoHs compliant

### Benefits

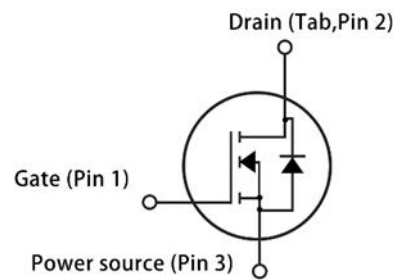
- Reduce switching losses
- Increased system Switching Frequency
- Increased power density
- Reduction of heat sink requirements

### Applications

- Switch mode power supplies
- Renewable energy
- On Board Charger
- High Voltage DC/DC Converters



TO-247



Ordering Part Number	Package	Brand
STW70N65M2	TO-247	HXY MOSFET

### Maximum Ratings ( $T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit	Note
$V_{DSmax}$	Drain-Source Voltage	$V_{GS} = 0V, I_D = 100\mu A$	650	V	
$V_{GSmax}$	Gate-Source voltage	AC ( $f > 1\text{ Hz}$ )	-10/+25	V	
$V_{GSop}$	Recommend Gate-Source Voltage	Static	-4/+20	V	
$I_D$	Continuous Drain current	$V_{GS} = 20V, T_C = 25^\circ\text{C}$	55	A	Fig. 14
		$V_{GS} = 20V, T_C = 100^\circ\text{C}$	39		
$I_{D,pulse}$	Pulsed Drain Current	Pulse with $t_p$ limited by $T_{jmax}$ at 1 ms Pulse with $t_p$ limited by $T_{jmax}$ at 100 $\mu s$	95 231	A	
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}, T_j = 175^\circ\text{C}$	208	W	Fig.16
$T_j$	Operating junction temperature		-55~175	$^\circ\text{C}$	
$T_{stg}$	Storage temperature		-55~175	$^\circ\text{C}$	
	TO-247 miunting torque	M3 Screw	0.7	Nm	



**Thermal Characteristics**

Symbol	Parameter	Value			Unit	Note
		Min.	Typ.	Max.		
$R_{th(jc)}$	Thermal resistance from Junction to Case		0.72		K/W	Fig. 15
$R_{th(ja)}$	Thermal resistance from Junction to Ambient		40		K/W	

**Electrical Characteristics** ( $T_c = 25^\circ\text{C}$  unless other wise specified)

**Static Characteristics**

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$V_{(BR)DSS}$	Drain-Source Breakdown voltage	$V_{GS} = 0V, I_D = 100\mu\text{A}$	650			V	
$V_{GS(th)}$	Gate Threshold voltage	$V_{GS} = V_{DS}, I_D = 5\text{mA}$		2.7		V	Fig. 9
		$V_{GS} = V_{DS}, I_D = 5\text{mA}, T_j = 175^\circ\text{C}$		1.8			
$I_{GSS}$	Gate-Source Leakage current	$V_{GS} = 20V, V_{DS} = 0V$			250	nA	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V, T_j = 25^\circ\text{C}$		1	50	$\mu\text{A}$	
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS} = 20V, I_D = 20\text{A}$		45	58	m $\Omega$	Fig. 3, 4, 5
		$V_{GS} = 20V, I_D = 20\text{A}, T_j = 175^\circ\text{C}$		60			
$g_{fs}$	Transconductance	$V_{DS} = 20V, I_D = 20\text{A}$		18		S	Fig. 6
		$V_{DS} = 20V, I_D = 20\text{A}, T_j = 175^\circ\text{C}$		11			



### Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$Q_{GS}$	Gate to Source Charge	$V_{DS} = 400V$ $I_D = 20A$ $V_{GS} = -4V/20V$		16.4		nC	Fig. 10
$Q_{GD}$	Gate to Drain Charge			16.5			
$Q_G$	Total Gate Charge			66.2			

### AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$C_{iss}$	Input Capacitance	$V_{GS} = 0V, V_{DS} = 600V$ $f = 1\text{ MHz}$ $V_{AC} = 25mV$		1410		pF	Fig. 13
$C_{oss}$	Output Capacitance			119		pF	
$C_{rss}$	Reverse Transfer Capacitance			4		pF	
$R_{G(int)}$	Internal Gate Resistance	$f = 1\text{ MHz}, V_{AC} = 25mV$		1.8		$\Omega$	

### Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$V_{SD}$	Diode Forward Voltage	$V_{GS} = -4V, I_{SD} = 8.8A$		3.7		V	Fig. 7,8
		$V_{GS} = -4V, I_{SD} = 8.8A, T_j = 175^\circ C$		3.1			
$I_S$	Continuous Diode Forward Current	$V_{GS} = -4V, T_C = 25^\circ C$		46		A	
$I_{S, pulse}$	Diode pulse Current	$V_{GS} = -4V$ , pulse width $t_p$ limited by $T_{jmax}$		95		A	



### Typical Performance

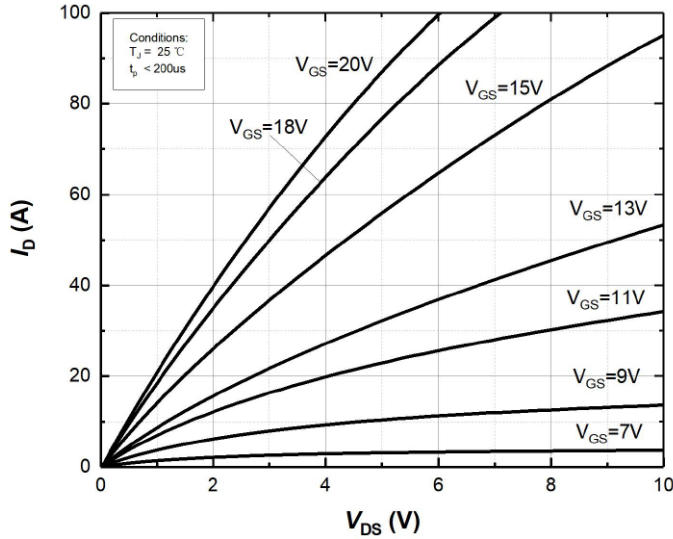


Figure 1. Output characteristics at  $T_j=25^\circ\text{C}$

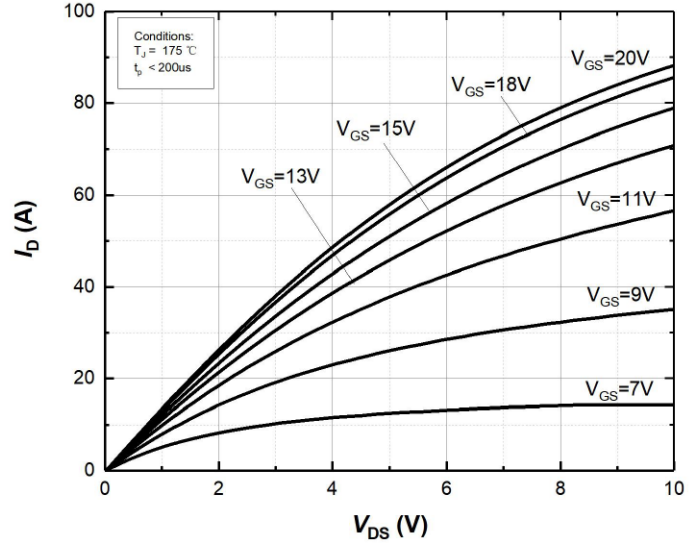


Figure 2. Output characteristics at  $T_j=175^\circ\text{C}$

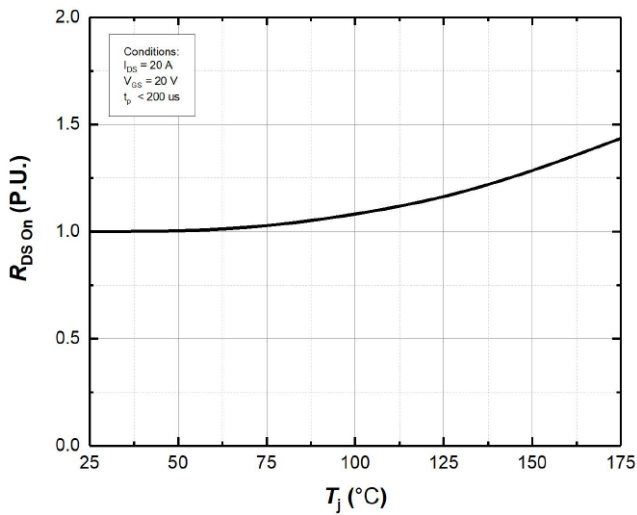


Figure 3. Normalized On-Resistance vs. Temperature

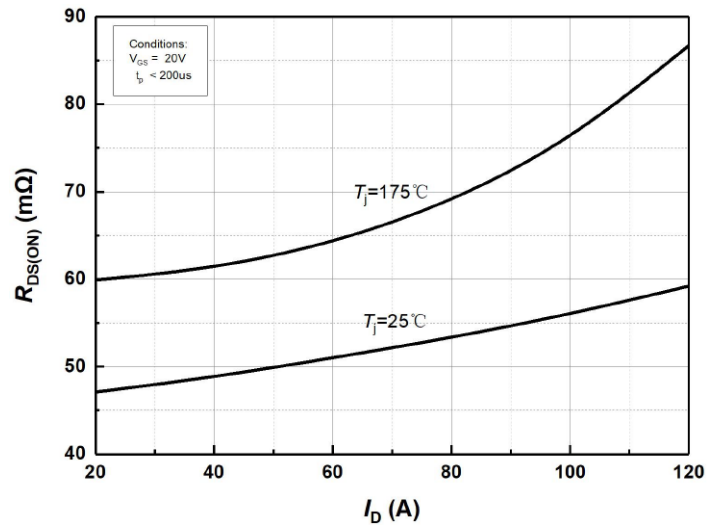


Figure 4. On-Resistance vs. Drain current for Various Temperature

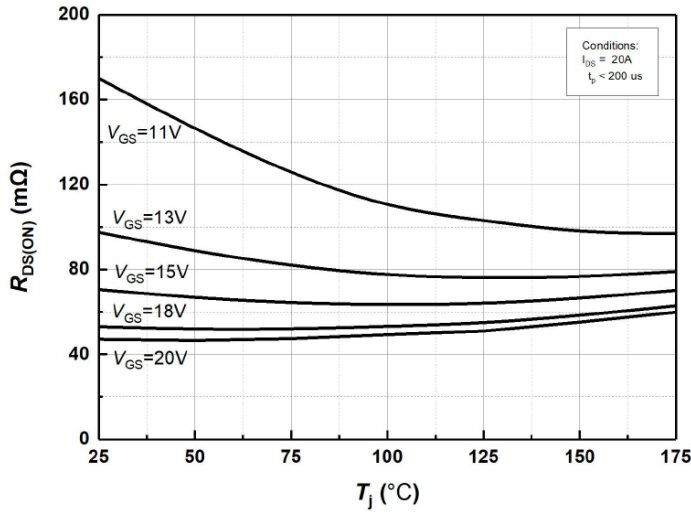


Figure 5. On-Resistance vs. Temperature for Various Gate Voltage

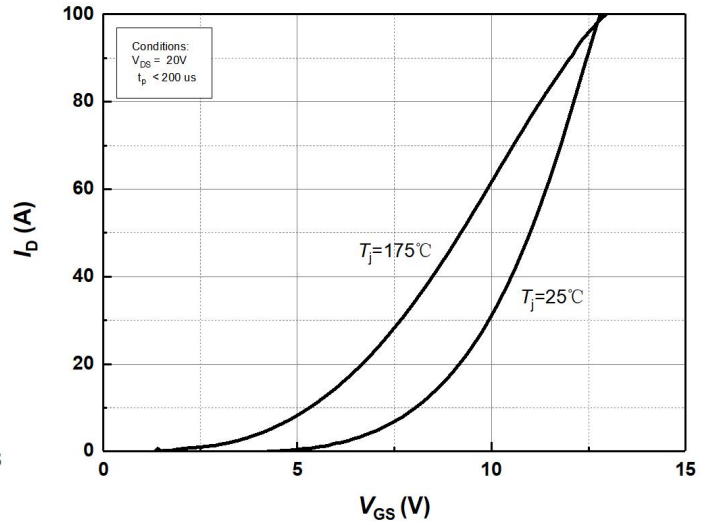


Figure 6. Transfer Characteristics for Various Junction Temperatures

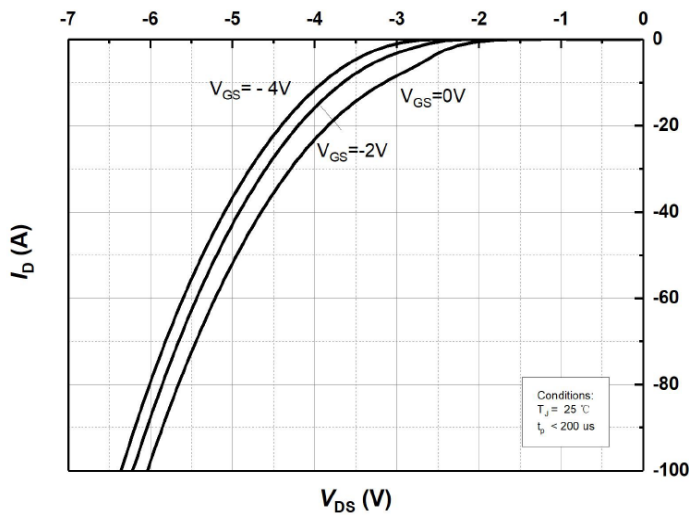


Figure 7. Body Diode Characteristics at  $T_j=25^\circ C$

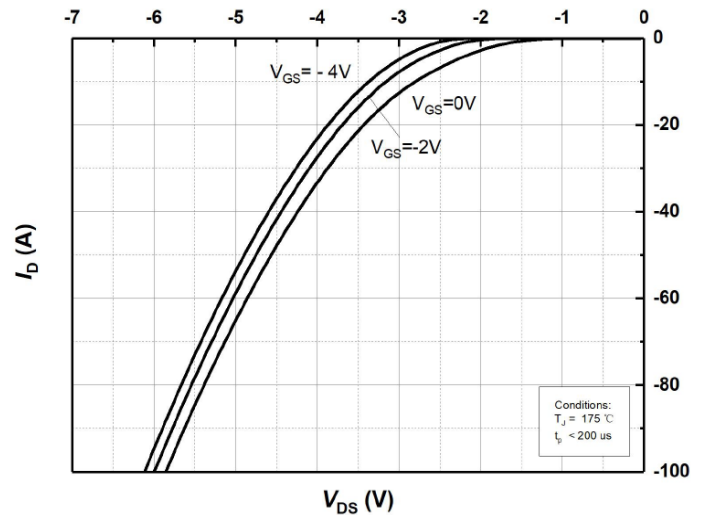


Figure 8. Body Diode Characteristics at  $T_j=175^\circ C$

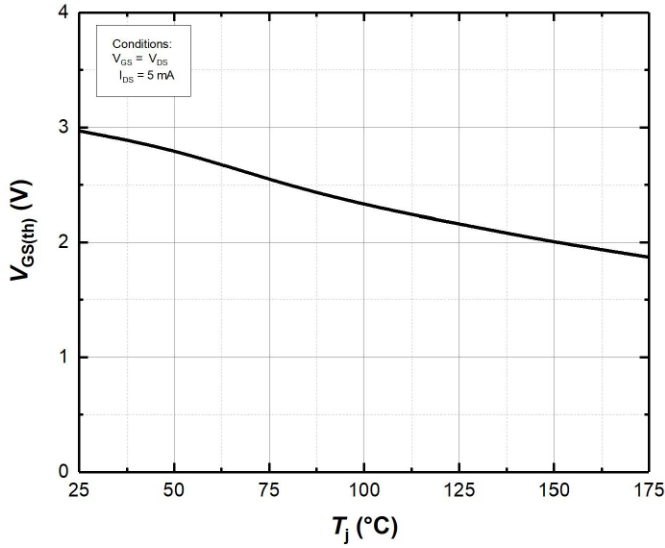


Figure 9. Threshold Voltage vs. Temperature

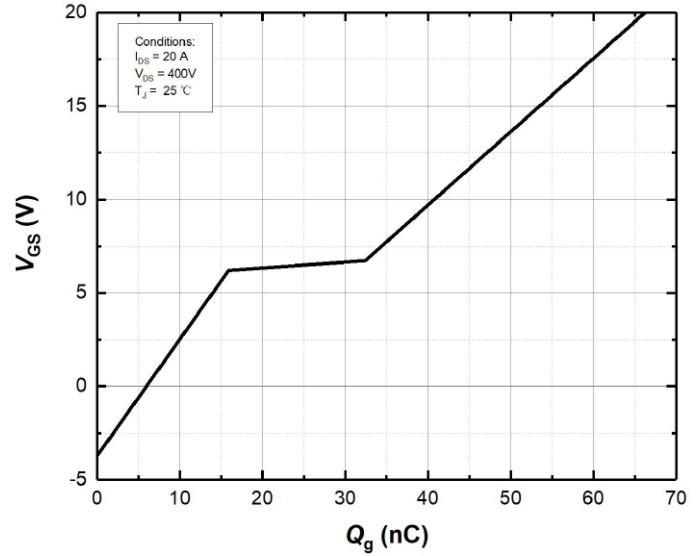


Figure 10 Gate Charge Characteristics

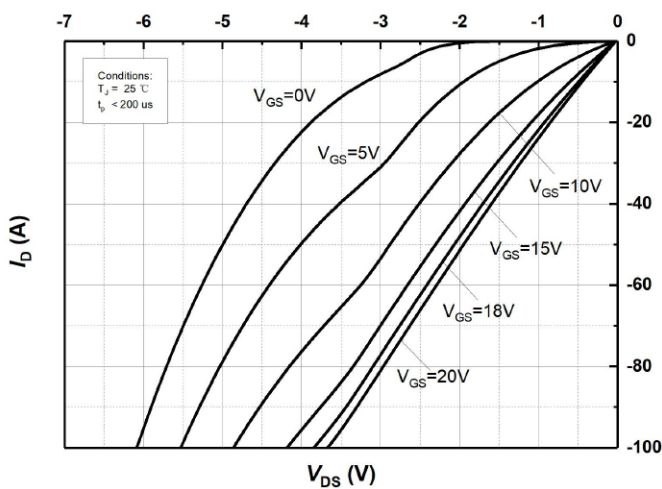


Figure 11. 3rd Quadrant Characteristic at  $T_j=25^\circ\text{C}$

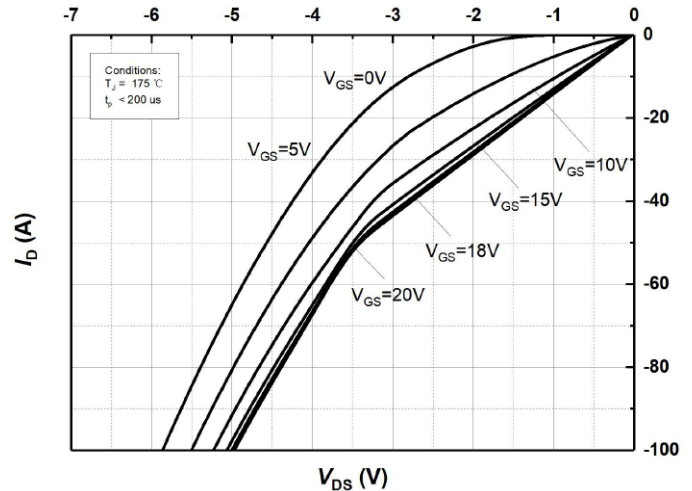


Figure 12. 3rd Quadrant Characteristic at  $T_j=175^\circ\text{C}$

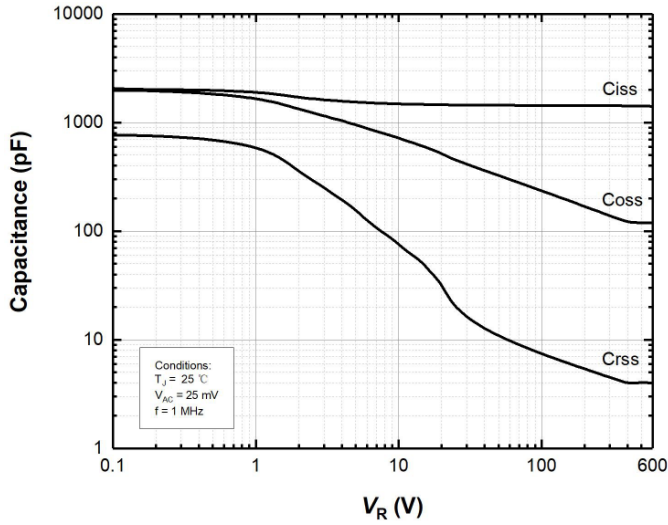


Figure 13. Capacitances vs. Drain-Source Voltage (0 – 600V)

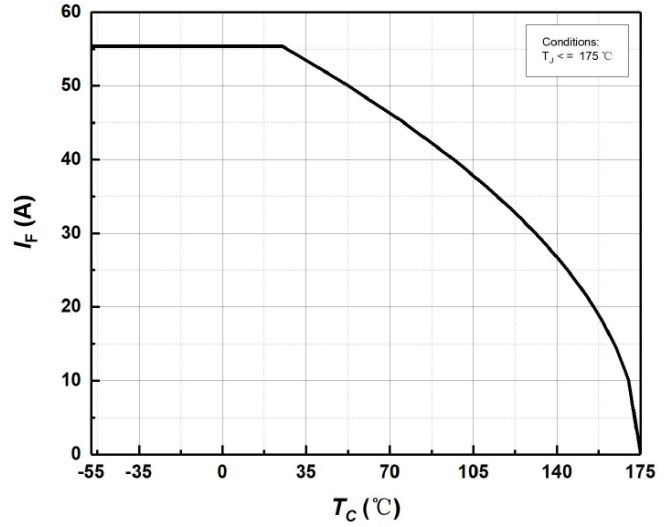


Figure 14. Continuous Drain Current Derating vs. Case Temperature

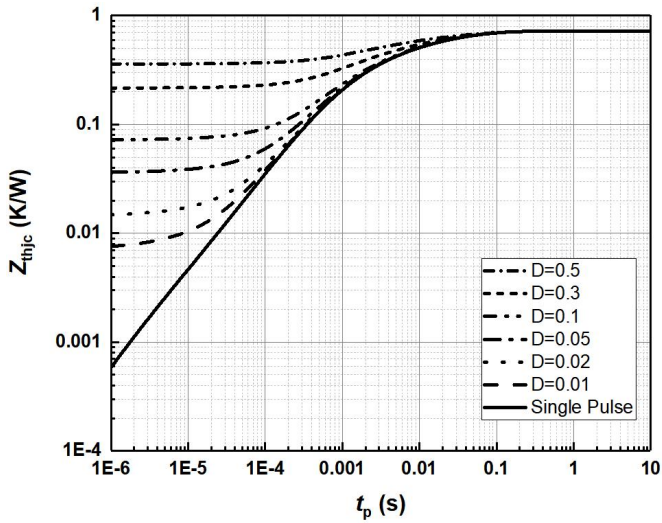


Figure 15. Transient Thermal Impedance (Junction – Case)

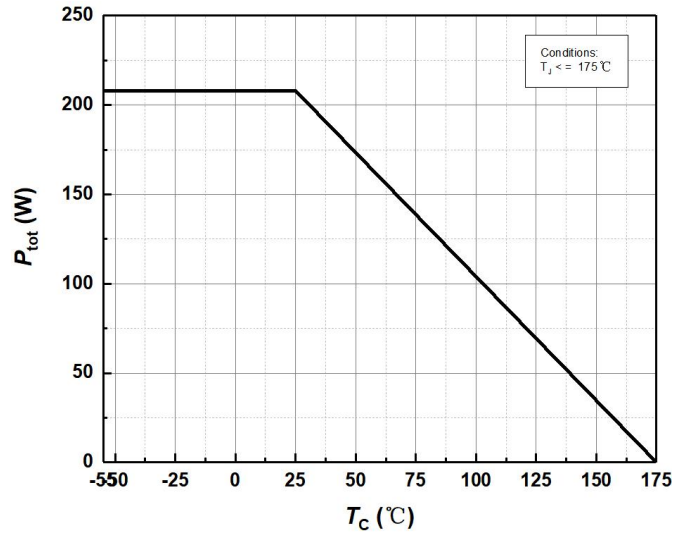


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature



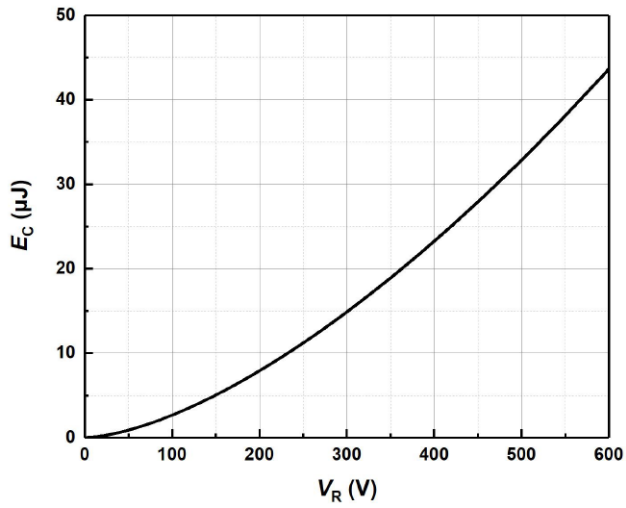


Figure 17. Output Capacitor Stored Energy

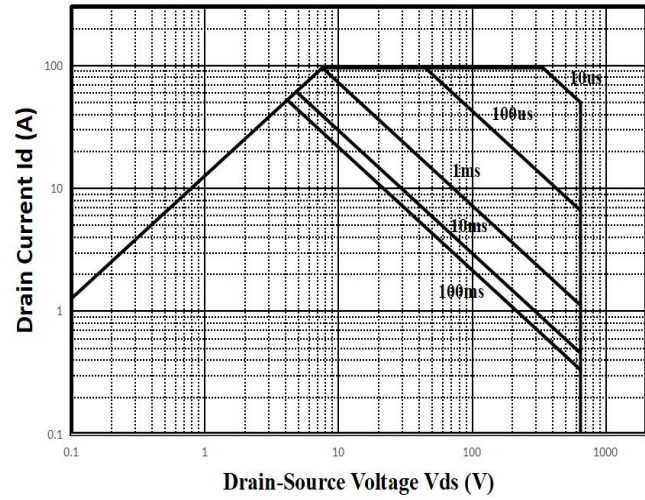


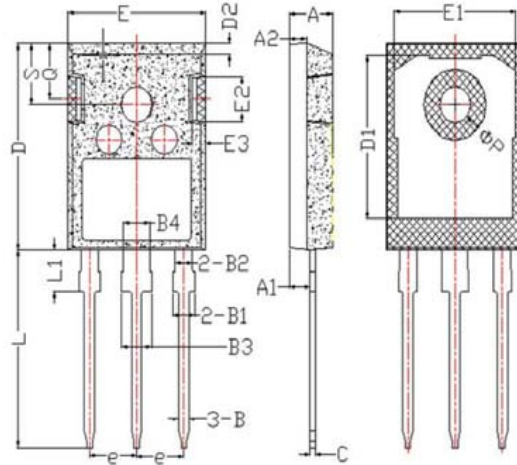
Figure 18. Safe Operating Area





## Package Dimensions

Package TO-247



Items	Values(mm)	
	MIN	MAX
A	4.6	5.2
A1	2.2	2.6
B	0.9	1.4
B1	1.75	2.35
B2	1.75	2.15
B3	2.8	3.35
B4	2.8	3.15
C	0.5	0.7
D	20.6	21.3
D1	16	18
E	15.5	16.1
E1	13	14.7
E2	3.8	5.3
E3	0.8	2.6
e	5.2	5.2
L	19	20.5
L1	3.9	4.6
Φp	3.3	3.7
Q	5.2	6
S	5.8	6.6



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